

PROGRAMMABLE CURRENT SENSING HIGH SIDE SWITCH

Features

- Load current feedback
- Programmable over current shutdown
- Active clamp
- E.S.D protection
- Input referenced to Vcc
- Reverse battery protection (reverse current operation)

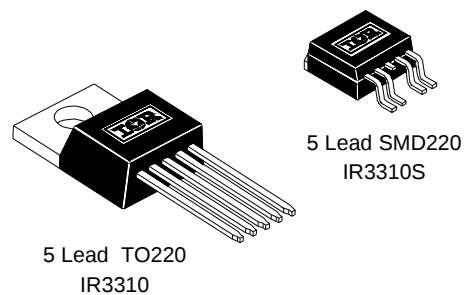
Description

The IR 3310 is a Fully Protected 4 terminal high side switch. The input signal is referenced to Vcc. When the input voltage $V_{cc} - V_{in}$ is higher than the specified V_{ih} threshold, the output power MOSFET is turned-on. When $V_{cc} - V_{in}$ is lower than the specified V_{il} threshold, the output MOSFET is turned-off. A sense current proportional to the current in the power Mosfet is sourced to the ST pin. Over-current shutdown occurs when $V_{st} - V_{in} > 4V$. Choosing R_{st} allows to adjust I_{sd} . Either over-current and over-temperature latches off the switch. The device is reset by pulling the input pin high. Other integrated protections (ESD, reverse battery, active clamp) make the IR 3310 very rugged and suitable for the automotive environment.

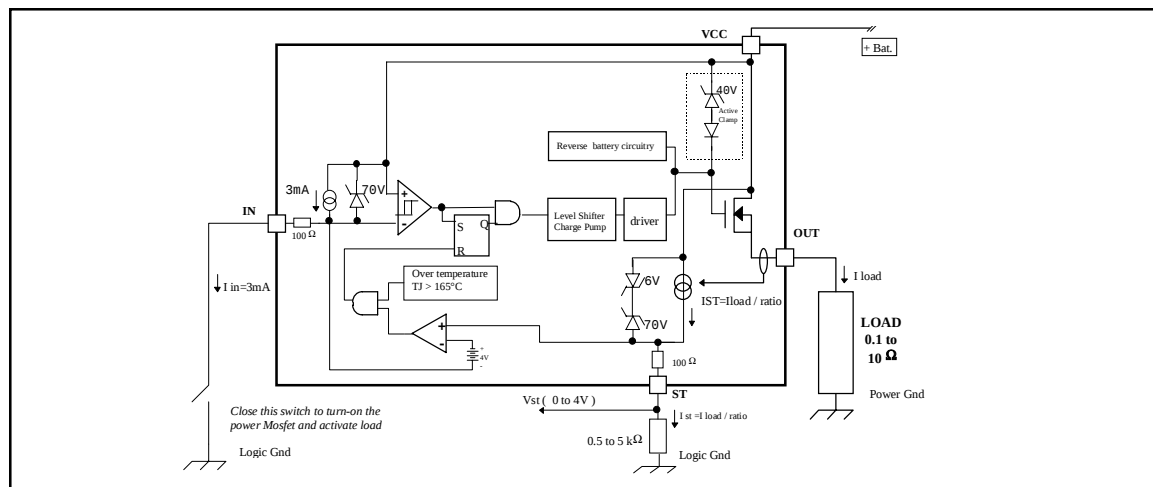
Product Summary

$R_{ds(on)}$	5m Ω typ.
$V_{cc.op.}$	5.5 to 35V
Current ratio	10 000
$I_{shutdown}$	10 to 100A
Active clamp	40V

Packages



Typical Connection



Absolute Maximum Ratings

Absolute maximum ratings indicates sustained limits beyond which damage to the device may occur. All voltage parameters are referenced to Vcc lead. (T_{Ambient} = 25°C unless otherwise specified).

Symbol	Parameter	Min.	Max.	Units
V _{cc} - V _{in} max	Maximum input voltage	-16	50	V
V _{cc} -V _{st} max	Maximum status voltage	-16	50	
V _{cc} - V _{out} max.	Maximum output voltage	-0.3	37	
I _{ds} cont.	Diode max. permanent current (R _{th} = 60 °C/W) (1)	—	2.8	A
I _{ds1} cont	Diode max. permanent current (R _{th} = 5 °C/W) (1)	—	35	
I _{ds} pulsed	Diode max. pulsed current (1)	—	100	
ESD 1	Electrostatic discharge (human body model)	—	tbd	kV
ESD 2	Electrostatic discharge (machine model)	—	tbd	
P _d	Power dissipation (R _{th} = 62 °C/W)	—	2	W
T _J max.	Max. storage and junction temperature	-40	150	°C
Min R _{st}	Minimum resistor on the ST pin	0.5	—	kΩ

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
R _{th} free air	Thermal resistance - free air	60	—	°C/W
R _{th} std footprint	Thermal resistance with standard footprint	80	—	°C/W
R _{th} 1" footprint	Thermal resistance with 1" footprint	50	—	°C/W
R _{th} junct. to case	Thermal resistance junction to case	5	—	°C/W

Recommended Operating Conditions

These values are given for a quick design. For operation outside these conditions, please consult the application notes.

Symbol	Parameter	Min.	Max.	Units
V _{cc} - V _{in}	Continuous input voltage	6	18	V
V _{cc} -V _{st}	Continuous status voltage	0	18	
V _{cc}	Supply to power ground voltage	6	18	
I _{out}	Continuous output current (R _{th} /amb < 5 °C/W, T _j = 125°C)	—	35	A
I _{out} 85°C amb.	Continuous output current (R _{th} /amb < 5 °C/W, T _j = 125°C)	—	8	
R _{st}	ST resistor to program I _{sd} and scale (2 & 3)	0.5	5	kΩ

Protection Characteristics

T_j = 25°C (unless otherwise specified), R_{st} = 500 to 5kΩ.

Symbol	Parameter	Typ.	Max.	Units	Test Conditions
V _{st} - V _{in} @ I _{sd}	Over-current shutdown threshold	4	—	V	
T _{sd}	Over-temp. shutdown threshold	165	—	°C	see Fig. 4
T _{reset}	Protection reset time	50	—	μS	see Fig. 4

- 1) Limited by junction temperature. Pulsed current is also limited by wiring
- 2) <500 Ohm or shorting ST to gnd may damage the part with I_{sd} around 120A
- 3) >5000 Ohm or leaving ST open will shutdown the part. No current will flow in the load.

Static Electrical Characteristics

(T_j = 25°C, V_{CC} = 14V unless otherwise specified.)

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I _q	Quiescent current	—	7	50	μA	V _{CC} -V _{in} =0, V _{CC} -V _{out} =12V
I _{in}	Input current	—	3	—	mA	V _{CC} -V _{in} =14V
V _{ih}	High level input threshold voltage (4)	—	5	—	V	
V _{il}	Low level input threshold voltage (4)	—	4	—		
V _{hys}	Input hysteresis = V _{ih} -V _{il}	—	1	—		
R _{ds1 on}	ON state resistance	—	5	—	mΩ	I _{out} =35A, V _{CC} =14V
R _{ds2 on}	ON state resistance	—	5.5	—		I _{out} =17A, V _{CC} -V _{in} =6V
R _{ds3 on}	ON state resistance	—	8	—		I _{out} =35A, T _j = 150°C
V _{clamp1}	V _{CC} to V _{out} active clamp voltage	37	40	—	V	I _{out} = 10mA
V _{clamp2}	V _{CC} to V _{out} active clamp voltage	—	42	48		I _{out} = 35mA
V _{sd}	Body diode forward voltage	—	0.85	1		I _d =35A, V _{CC} -V _{in} =0V

Switching Electrical Characteristics

V_{CC} = 14V, Resistive Load = 0.4Ω, T_j = 25°C, (unless otherwise specified).

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
T _{on}	Turn-on delay time to V _{cc} -V _{out} = 0.9 V _{cc}	—	10	—	μs	see figure 2
T _{r1}	Rise time to V _{cc} -V _{out} =5V	—	16	—		
T _{r2}	Rise time from end of T _{r1} to V _{out} = 10% of V _{cc}	—	300	—		
dV/dt (on)	Turn ON dV/dt	—	1.2	—	V/μs	
E _{on}	Turn ON energy	—	40	—	mJ	see figure 3
T _{off}	Turn-off delay time	—	tbd	—	μs	
T _f	Fall time to V _{cc} -V _{out} 90% of V _{cc}	—	tbd	—		
dV/dt (off)	Turn OFF dV/dt	—	tbd	—	V/μs	
E _{off}	Turn OFF energy	—	5	—	mJ	

Current Sense Characteristics

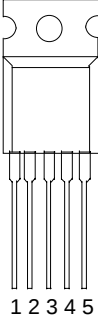
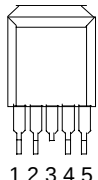
Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
Ratio	I _{load} / I _{status}	—	10,000	—	—	T _j = 25°C, R _{st} = 500Ω, I = 100A
Ratio	Gain variation over temperature range error T _{oC}	-5	—	+5	%	T _j = 40 To +150°C
offset	status current when I _{load} = 0	-0.5	0	+0.5	mA	T _j = 25°C, R _{st} = 500Ω, I = 100A
offset	Offset variation over temperature range var. T _{oC}	-0.4	0	0.4	mA	T _j = 40 To +150°C
T _{rst}	status response time to a small I _{load} step		10		μs	to get 90% of the I _{load} step

4) Input threshold are measured directly between the input pin and the tab. Any parasitic resistance in common between the load current path and the input signal path can significantly affect the thresholds.

IR3310

International
IR Rectifier

Lead Assignments

	1 - In 2 - ST 3 - Vcc (tab) 4 - NC 5 - Out	
5 Lead - TO220		5 Lead - SMD220
IR3310		IR3310S
Part Number		

The following note applies to all curves: 1) they are all typical characteristics. 2) Operation in shaded area is not recommended. 3) $T_j = 25^{\circ}\text{C}$, $R_{st}=500\Omega$, $V_{bat}=14\text{V}$ (unless otherwise specified).

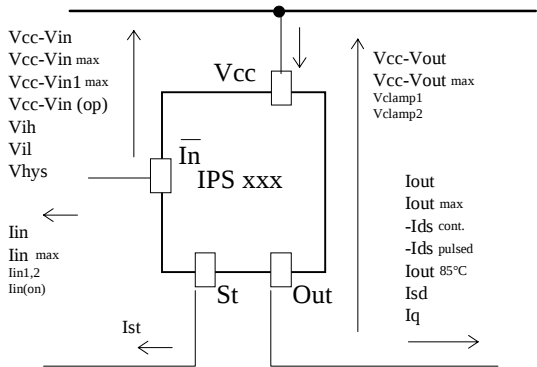


Figure 1 - Voltages and currents definition

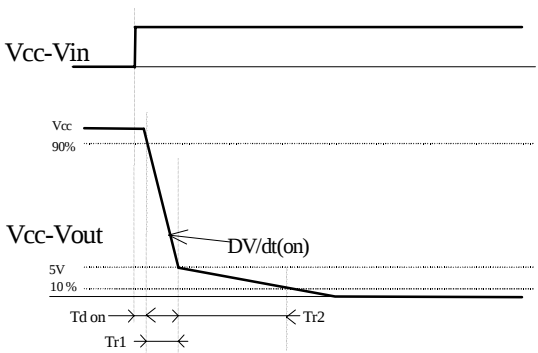


Figure 2 - Switching time definitions (turn-on)

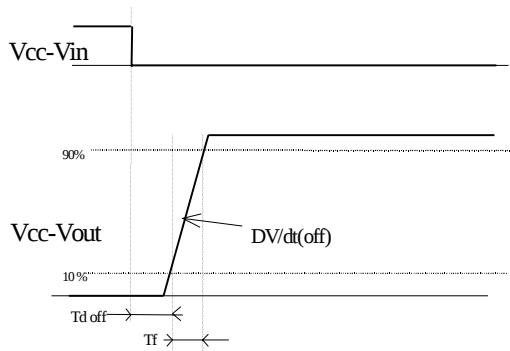


Figure 3 - Switching time definitions (turn-off)

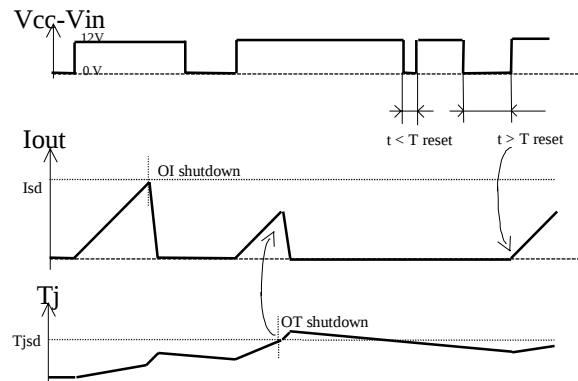
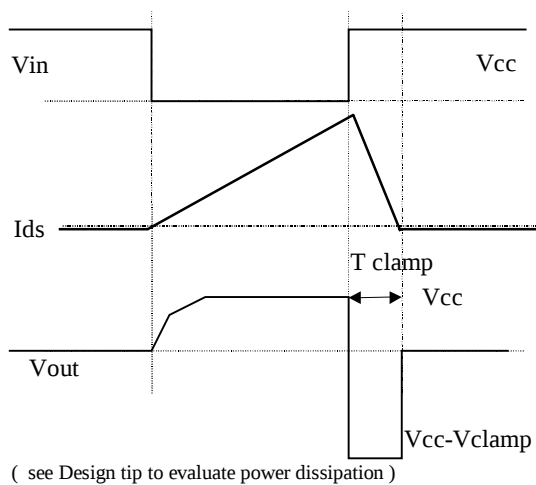


Figure 4 - Protection timing diagram



(see Design tip to evaluate power dissipation)

Figure 5 - Active clamp waveform

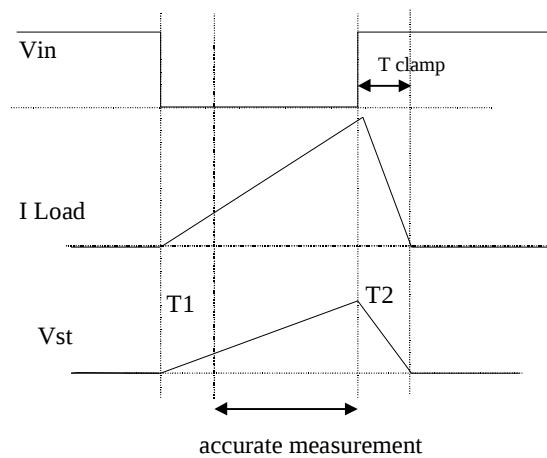


Fig 6 - Current sensing accuracy:
Measurement is accurate only when the power Mosfet is fully on (outside $T_1=T_{don} + T_{r1}+T_{r2}$) and when the part is not in the active clamp (outside T_2).

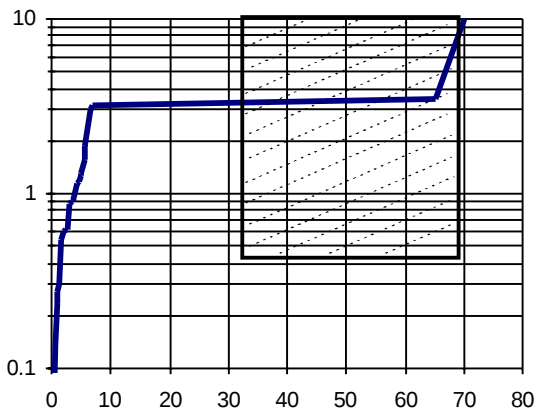


Figure 7 - Icc (mA) vs Vcc-Vin (V)

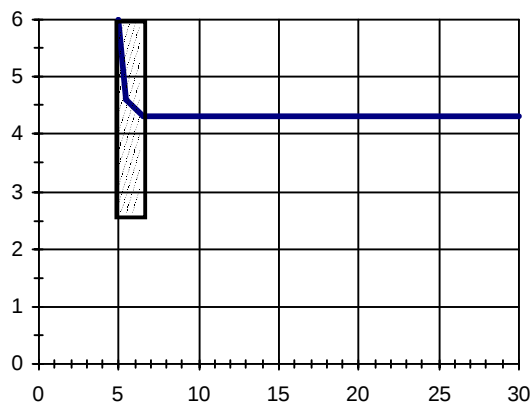


Figure 8 - RdsOn (mΩ) vs Vcc-Vin (V)

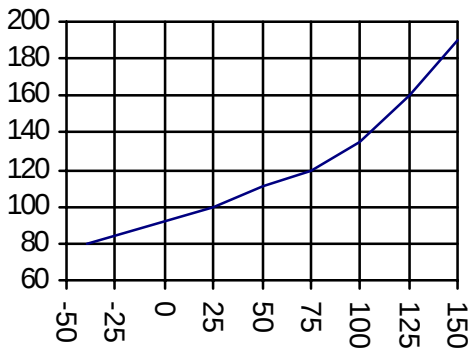


Figure 9 - Normalized Rdson (%) vs Tj (°C)

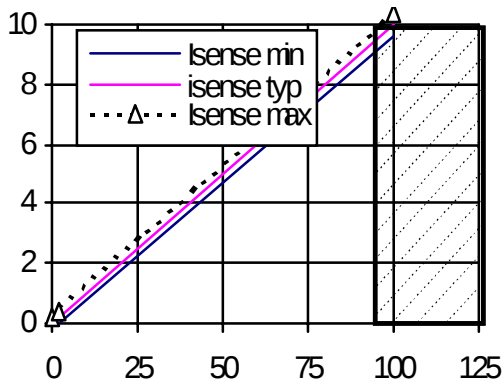
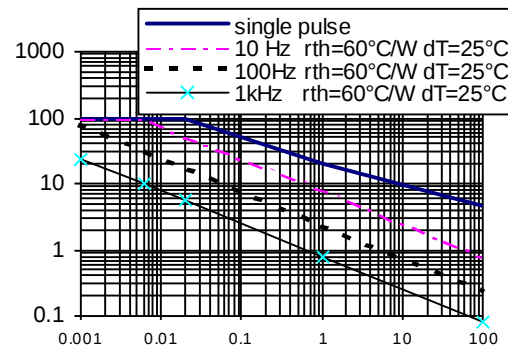
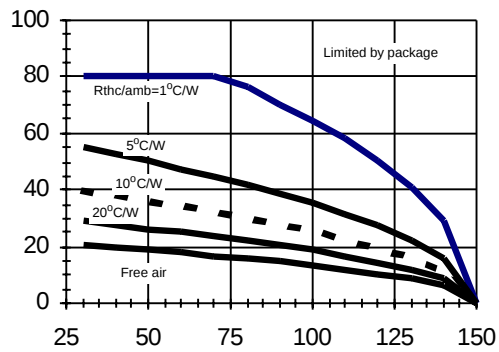
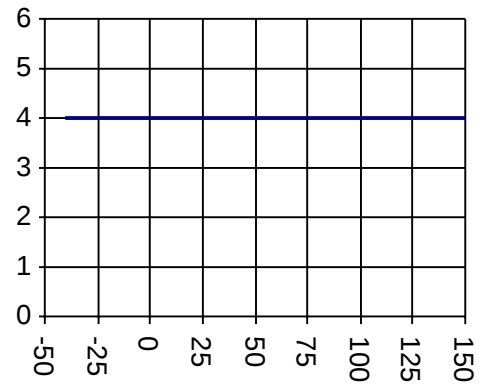
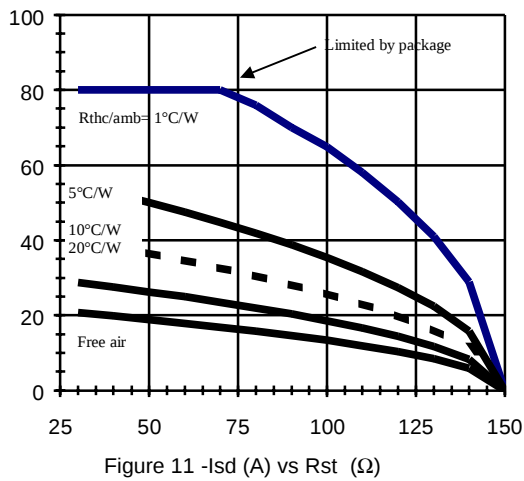


Figure 10 - Isense (mA) vs Iload (A)



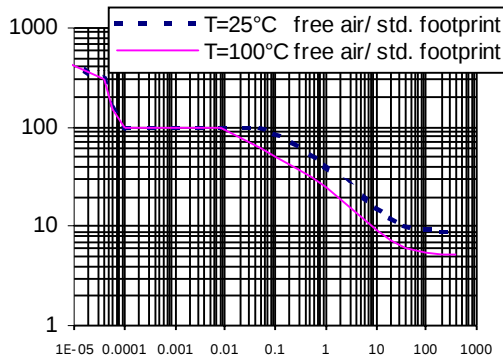


Figure 15 - I out (A) vs Protection resp. Time (s)

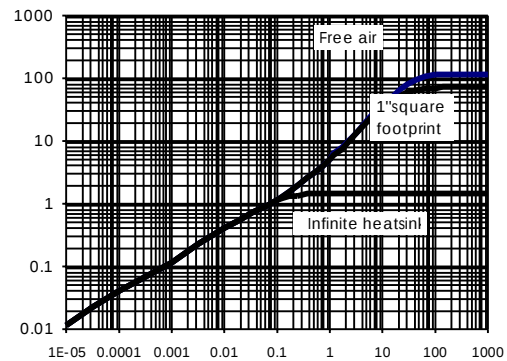


Figure 16 - Transient Rth (°C) vs Time (s)

How to use the IR 3310 device

- Check max. continuous power dissipation :

Use figure 11 to check that max. continuous load current does not exceed the device capability in worst case ambient temperature.

- Choose Isd so that it exceeds the maximum transient current with a sufficient margin.
I max. load shall not exceed 100A.

- Choose Rst to get Isd by mean of fig. 10 curve or using the following formula

$$I_{sd} = (V_{st} - V_{in @ I_{sd}}) * gain / R_{st} = 4V * 10000 / R_{st}.$$

This ensures optimum protection and full scale of Vst signal (0V for I load=0 and 4V for I load = Isd).

- To reduce power dissipation during reverse battery operation, the inner circuitry takes the potential available on ST pin in order to turn on the power MOSFET. This principle works only if Rst is within the recommended range (0.5 to 5 kΩ) and Rev.bat. voltage > 5V.

Also, the logic Gnd must not be disconnected from the Power Gnd (due to another reverse battery protection circuitry for example).

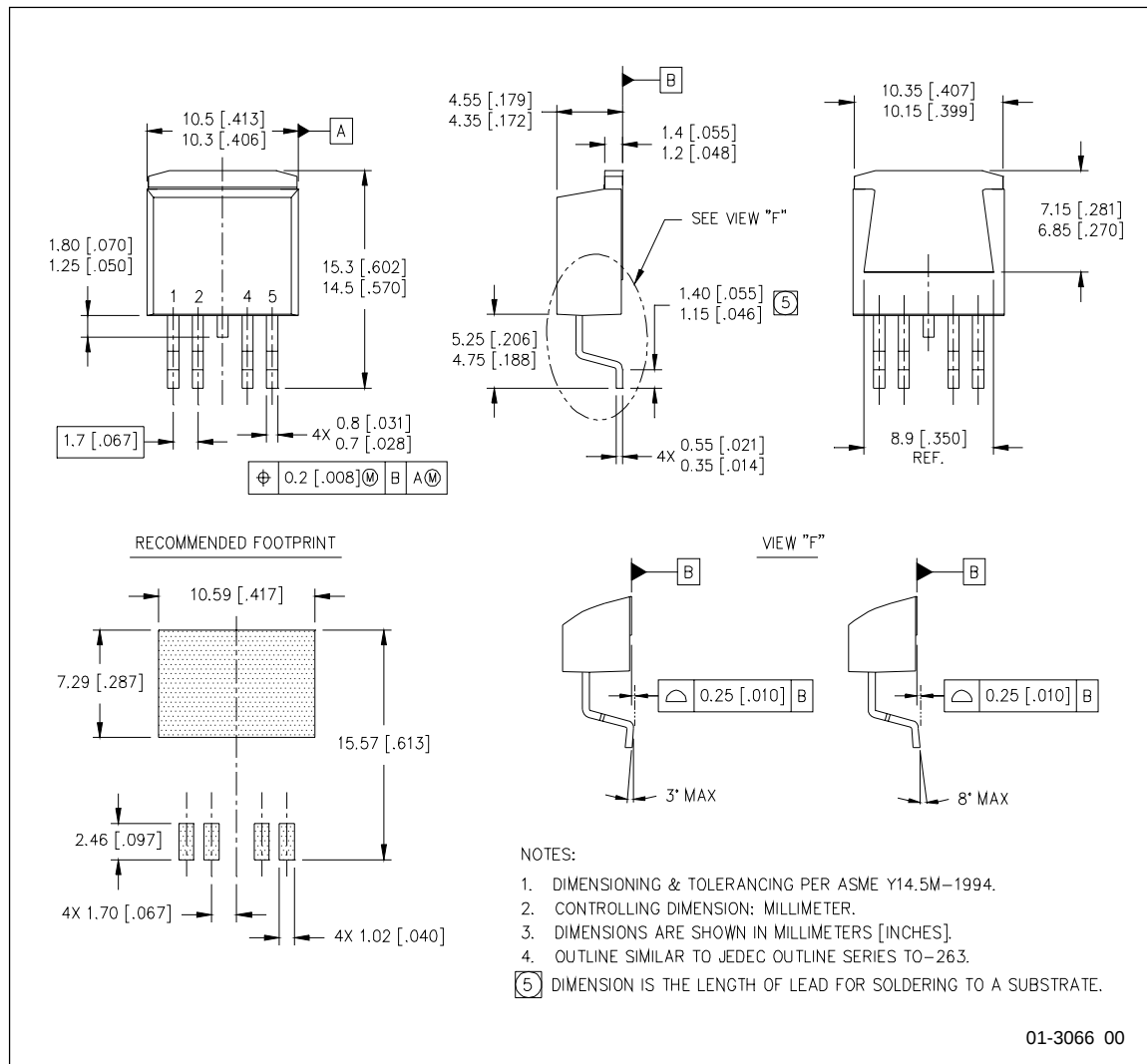
Check that junction temperature does not exceed the max. value (165°C) :

$$(\text{losses multiplied by } r_{th} + \text{max. ambient}) < 165^{\circ}\text{C}.$$

$$\text{Total Losses (w)} = P_{\text{power Mosfet}} + P_{(in)} + P_{(st)}$$

[illegible]

Case Outline - D²PAK (SMD220) - 5 Lead



Tape & Reel - SMD220 - 5 Lead

